

ISP817X,ISP827X,ISP847X3,2,1
ISP817,ISP827,ISP847-3,-2,-1



**LOW INPUT CURRENT
PHOTOTRANSISTOR
OPTICALLY COUPLED ISOLATORS**

APPROVALS

- UL recognised, File No. E91231
- **'X' SPECIFICATION APPROVALS**
 - VDE 0884 in 3 available lead form : -
- STD
- G form
- SMD approved to CECC 00802
- Certified to EN60950 by the following Test Bodies :-
Nemko - Certificate No. P01102465
Fimko - Certificate No. FI18162
Semko - Reference No. 0202041/01-25
Demko - Certificate No. 311161-01
- BSI approved - Certificate No. 8001

DESCRIPTION

The ISP817-3,-2,-1, ISP827-3,-2,-1, ISP847-3,-2,-1 series of optically coupled isolators consist of infrared light emitting diodes and NPN silicon photo transistors in space efficient dual in line plastic packages.

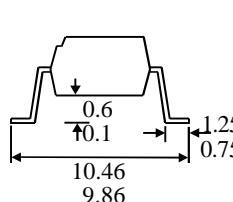
FEATURES

- Options :-
10mm lead spread - add G after part no.
Surface mount - add SM after part no.
Tape&reel - add SMT&R after part no.
- Low input current 0.5mA I_F
- High Current Transfer Ratio (50% min)
- High Isolation Voltage (5.3kV_{RMS}, 7.5kV_{PK})
- High BV_{CEO} (70V min)
- All electrical parameters 100% tested
- Custom electrical selections available

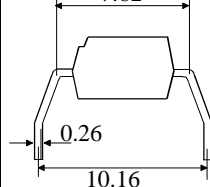
APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances

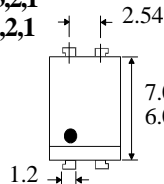
**OPTION SM
SURFACE MOUNT**



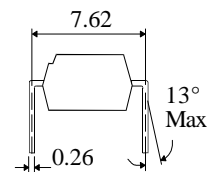
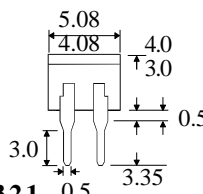
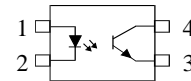
OPTION G



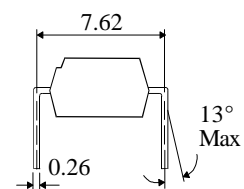
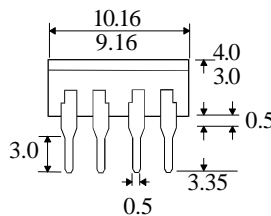
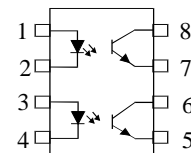
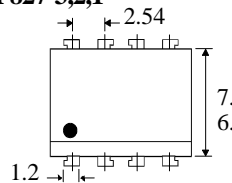
**ISP817X3,2,1
ISP817-3,2,1**



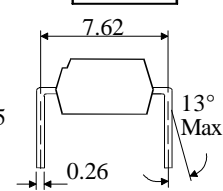
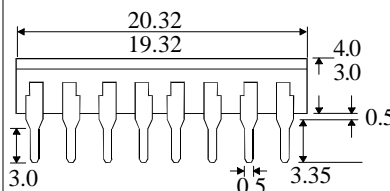
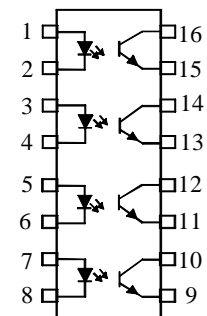
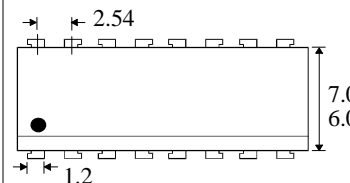
Dimensions in mm



**ISP827X3,2,1
ISP827-3,2,1**



**ISP847X3,2,1
ISP847-3,2,1**



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ABSOLUTE MAXIMUM RATINGS
(25°C unless otherwise specified)

Storage Temperature	-55°C to + 125°C
Operating Temperature	-30°C to +100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)	260°C

INPUT DIODE

Forward Current	50mA
Reverse Voltage	6V
Power Dissipation	70mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV_{CEO}	70V
Emitter-collector Voltage BV_{ECO}	6V
Power Dissipation	150mW

POWER DISSIPATION

Total Power Dissipation	200mW
(derate linearly 2.67mW/°C above 25°C)	

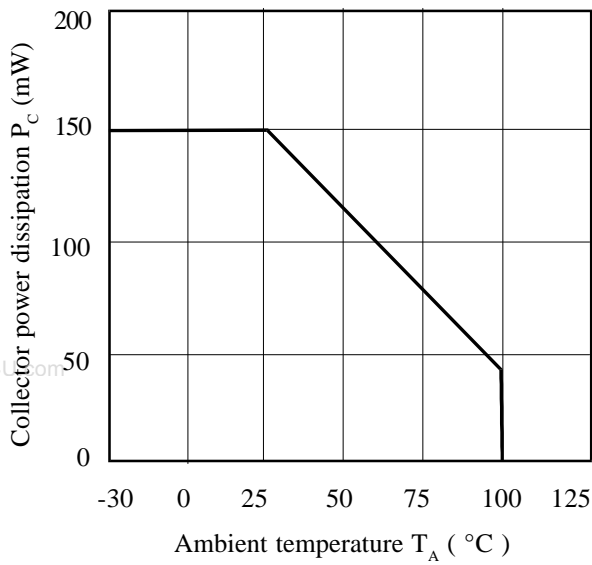
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)		1.2	1.4	V	$I_F = 20\text{mA}$
	Reverse Current (I_R)			10	μA	$V_R = 4\text{V}$
Output	Collector-emitter Breakdown (BV_{CEO}) (Note 2)	70			V	$I_C = 1\text{mA}$
	Emitter-collector Breakdown (BV_{ECO})	6			V	$I_E = 10\mu\text{A}$
	Collector-emitter Dark Current (I_{CEO})			100	nA	$V_{CE} = 20\text{V}$
Coupled	Current Transfer Ratio (CTR) (Note 2)				%	
	ISP817-3, ISP827-3, ISP847-3	70			%	$0.5\text{mA } I_F, 0.4\text{V } V_{CE}$
		100			%	$1.0\text{mA } I_F, 0.4\text{V } V_{CE}$
	ISP817-2, ISP827-2, ISP847-2	50			%	$0.5\text{mA } I_F, 0.4\text{V } V_{CE}$
	ISP817-1, ISP827-1, ISP847-1	50			%	$1.0\text{mA } I_F, 0.4\text{V } V_{CE}$
	Collector-emitter Saturation Voltage -3			0.4	V	$0.5\text{mA } I_F, 0.35\text{mA } I_C$
	-2			0.4	V	$0.5\text{mA } I_F, 0.25\text{mA } I_C$
	-1			0.4	V	$1.0\text{mA } I_F, 0.5\text{mA } I_C$
	Input to Output Isolation Voltage V_{ISO}	5300 7500			V_{RMS} V_{PK}	See note 1 See note 1
	Input-output Isolation Resistance R_{ISO}	5×10^{10}			Ω	$V_{IO} = 500\text{V}$ (note 1)
Output Rise Time t_r		4	18	μs	$V_{CE} = 2\text{V}$,	
Output Fall Time t_f		3	18	μs	$I_C = 0.2\text{mA}, R_L = 100\Omega$	

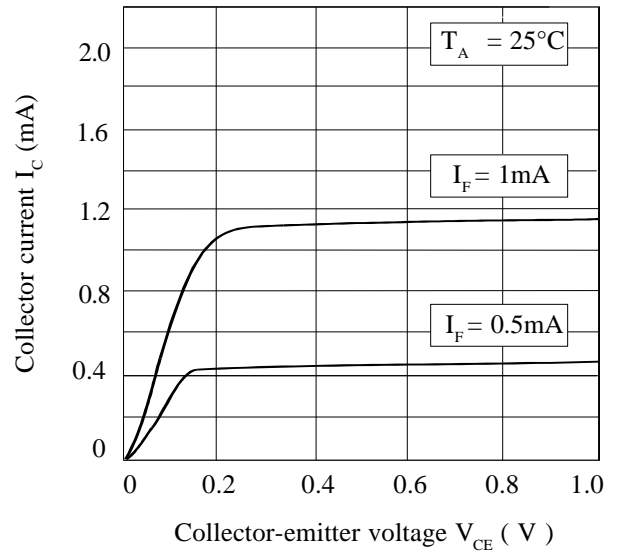
Note 1 Measured with input leads shorted together and output leads shorted together.

Note 2 Special Selections are available on request. Please consult the factory.

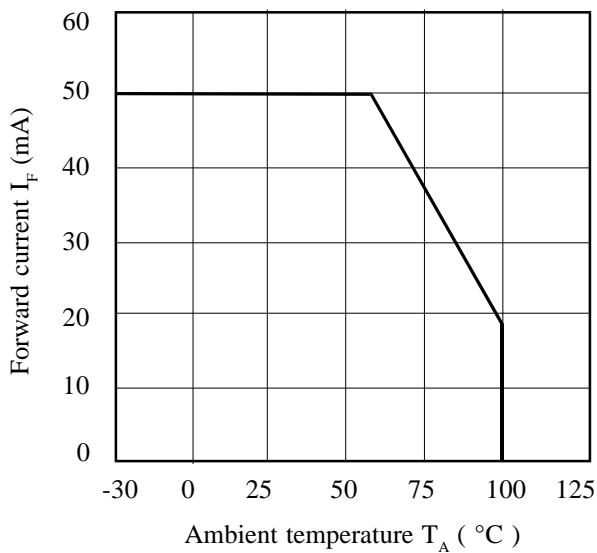
Collector Power Dissipation vs. Ambient Temperature



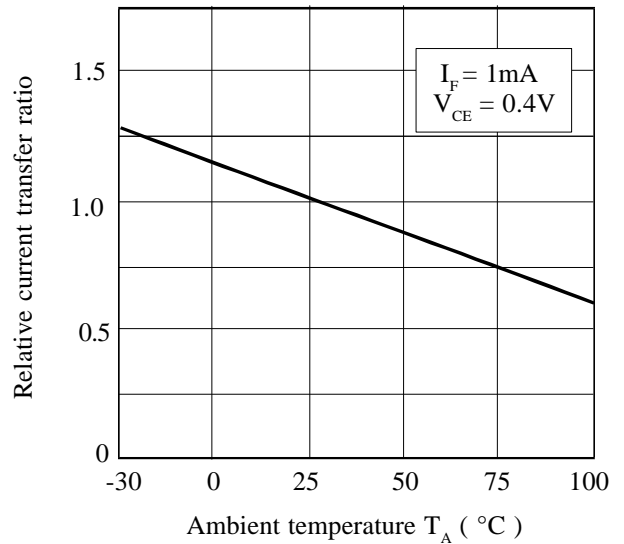
Collector Current vs. Low Collector-emitter Voltage



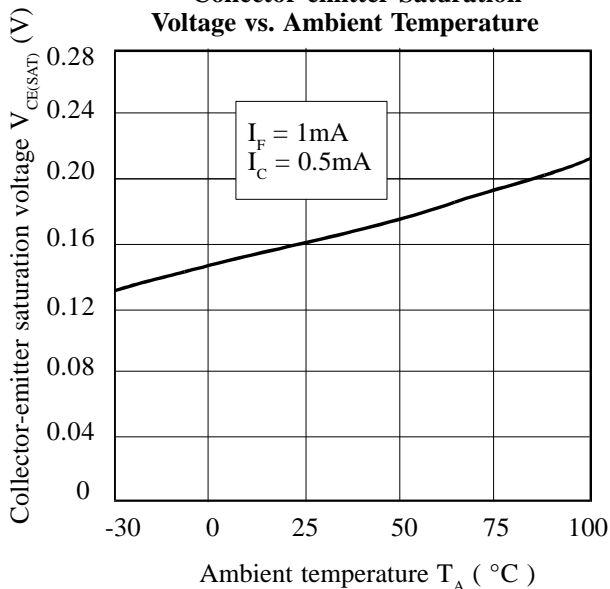
Forward Current vs. Ambient Temperature



Relative Current Transfer Ratio vs. Ambient Temperature



Collector-emitter Saturation Voltage vs. Ambient Temperature



Current Transfer Ratio vs. Forward Current

